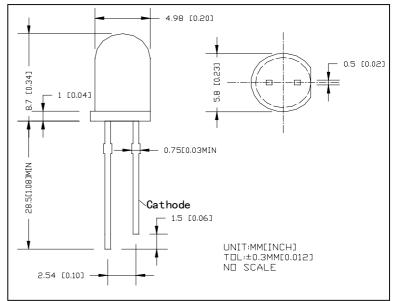


### DESCRIPTION

MBB51TK-11J is an ultra high brightness InGaN/GaN blue LED lamp encapsulated in a 5mm diameter clear transparent lens.



### ABSOLUTE MAXIMUM RATINGS

Power Dissipation @ Ta=25°C Continuous Forward Current Reverse Voltage Operating Temperature Range Storage Temperature Range Lead Soldering Temperature (1/16" from body)

125mW 30mA 5V -20 to +80°C -30 to +100°C 260°C for 5 sec.

## **ELECTRO-OPTICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage	VF		3.2	3.5	V	IF=20mA
Reverse Breakdown Voltage	BVR	5			V	IR=100µA
Viewing Angle	20 1/2		70		degree	IF=20mA
Luminous Intensity	IV	3500	4200		mcd	IF=20mA
Dominant Wavelength	λd	465		470	nm	IF=20mA
Spectral Line Half Width	Δλ		30		nm	IF=20mA

CAUTION

Static eletricity and surge damages the LED ,It is recommended to use a wrist band or anti-eletrostatic glove when handling the LED . All devices, equipment and machinery must be properly grounded.

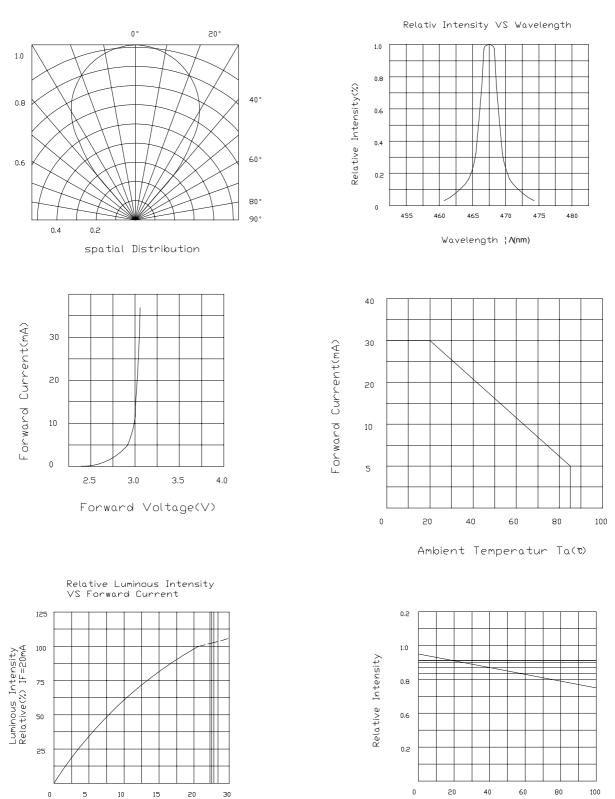


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# **MBB51TK-11J**

## Typical Electro-Optical Characteristics Curves(Ta=25°C)



Forward Current(mA)

Ambient Temperatur Ta(v)

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